

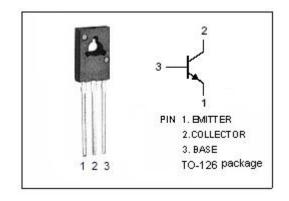
## **isc Silicon NPN Power Transistor**

### **DESCRIPTION**

- · High Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 250V(Min)
- High Current-Gain Bandwidth Product
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

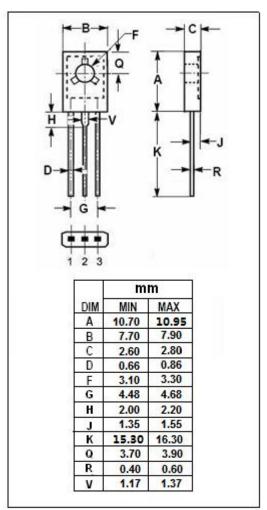
#### **APPLICATIONS**

- For high breakdown voltage general amplification
- For video output amplification



# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL           | PARAMETER  | VALUE   | UNIT       |  |
|------------------|--|---------|------------|--|
| V <sub>CBO</sub> | Collector-Base Voltage                               | 250     | V          |  |
| V <sub>CEO</sub> | Collector-Emitter Voltage                            | 250     | V          |  |
| V <sub>EBO</sub> | Emitter-Base Voltage                                 | 7       | V          |  |
| Ic               | Collector Current-Continuous                         | 0.1     | Α          |  |
| Ісм              | Collector Current-Peak 0.15                          |         | А          |  |
| Pc               | Collector Power Dissipation @ $T_C$ =25 $^{\circ}$ C | 4       | W          |  |
|                  | Collector Power Dissipation @ T <sub>a</sub> =25℃    | 1.2     |            |  |
| TJ               | Junction Temperature                                 | 150     | $^{\circ}$ |  |
| T <sub>stg</sub> | Storage Temperature Range                            | -55~150 | °C         |  |





## **isc Silicon NPN Power Transistor**

2SC2258

#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

| SYMBOL               | PARAMETER                            | CONDITIONS  | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|---|-----|------|-----|------|
| V <sub>(BR)EBO</sub> | Emitter-Base Breakdown Vltage        | I <sub>E</sub> = 0.1mA ; I <sub>C</sub> = 0                             | 7   |      |     | V    |
| V <sub>CE(sat)</sub> | Collector-Emitter Saturation Voltage | I <sub>C</sub> = 50mA; I <sub>B</sub> =5mA                              |     |      | 1.2 | V    |
| V <sub>BE(on)</sub>  | Collector-Emitter On Voltage         | I <sub>C</sub> = 40mA ; V <sub>CE</sub> = 20V                           |     |      | 1.2 | V    |
| I <sub>CER</sub>     | Collector Cutoff Current             | V <sub>CE</sub> = 250V; R <sub>BE</sub> = 100k Ω                        |     |      | 100 | μА   |
| h <sub>FE-1</sub>    | DC Current Gain                      | I <sub>C</sub> = 40mA ; V <sub>CE</sub> = 20V                           | 40  |      |     |      |
| h <sub>FE-2</sub>    | DC Current Gain                      | I <sub>C</sub> = 5mA ; V <sub>CE</sub> = 50V                            | 30  |      |     |      |
| fτ                   | Current-Gain—Bandwidth Product       | I <sub>E</sub> = -10mA;V <sub>CB</sub> = 10V;f <sub>test</sub> = 200MHz |     | 100  |     | MHz  |
| Сов                  | Output Capacitance                   | I <sub>E</sub> = 0; V <sub>CB</sub> = 50V,f <sub>test</sub> = 1MHz      |     | 3    |     | pF   |

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